Philips Semiconductors

Product specification

Rectifier diodes schottky barrier

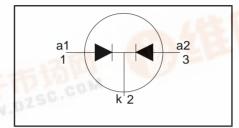
PBYR4025WT series

FEATURES

- Low forward volt drop
- Fast switching
- Reverse surge capability
- High thermal cycling performance
- · Low thermal resistance

SYMBOL

WWW.DZSC.



QUICK REFERENCE DATA

$$V_R = 20 \text{ V} / 25 \text{ V}$$
 $I_{O(AV)} = 40 \text{ A}$
 $V_F \le 0.46 \text{ V}$

GENERAL DESCRIPTION

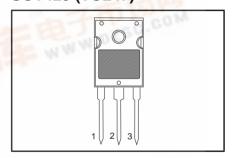
Dual, common cathode schottky rectifier diodes in a plastic envelope. Intended for use as output rectifiers in low voltage, high frequency switched mode power supplies.

PBYR4025WT series is supplied in the conventional leaded SÖT429 (TO247) package.

PINNING

PIN	DESCRIPTION		
1	anode 1 (a)		
2	cathode (k)		
3	anode 2 (a)		
tab	cathode		

SOT429 (TO247)



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.		UNIT
			1727	-20	-25	
V_{RRM}	Repetitive peak reverse voltage	300	100	20	25	V
V_{RWM}	Crest working reverse voltage		-	20	25	V
V_R	Continuous reverse voltage	T _{mb} ≤ 109 °C	-	20	25	V
$I_{O(AV)}$	Average output current (both diodes conducting)	square wave; $\delta = 0.5$; $T_{mb} \le 128 ^{\circ}\text{C}$	-	4	0	А
I _{FRM}		$t = 25 \mu s; δ = 0.5;$ $T_{mb} \le 128 °C$	-	4	0	А
I _{FSM}	Non-repetitive peak forward	t = 10 ms	-	18	30	Α
	current, per diode	t = 8.3 ms	-	20	00	Α
	·	sinusoidal T _j = 125 °C prior to surge; with reapplied	-	由于		A,
		V _{RRM(max)}		COLUMN T	J.L.	
I _{RRM}	Repetitive peak reverse current per diode	$t_p = 2 \mu s; \delta = 0.001$	NET	M. a	2	A
T_{stg}	Storage temperature		-65		75	°C
T _i ~	Operating junction temperature	7179	-	15	50	°C

THERMAL RESISTANCES						
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-mb}	Thermal resistance junction to mounting base Thermal resistance junction to ambient	per diode both diodes in free air	- - -	- - 45	1.5 1.0 -	K/W K/W K/W



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STATIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _F	Forward voltage (per diode)	I _F = 20 A; T _j = 125°C I _F = 40 A; T _j = 125°C	-	0.40	0.46	V
		$I_{\rm F} = 40 \text{ A}; T_{\rm i} = 125^{\circ}\text{C}$	-	0.50	0.54	V
		$I_{\rm F} = 40 {\rm A}$	-	0.60	0.64	V
I _R	Reverse current (per diode)	$V_R = V_{RRM}$	-	2.0	10	mA
	, ,	$V_{R}^{A} = V_{RRM}^{AAA}$; $T_{i} = 100 ^{\circ}C$	-	30	80	mA
C _d	Junction capacitance (per diode)	$V_R = V_{RRM}^{NNM}$; $T_j = 100 ^{\circ}\text{C}$ $f = 1\text{MHz}$; $V_R = 5\text{V}$; $T_j = 25 ^{\circ}\text{C}$ to	-	900	-	pF

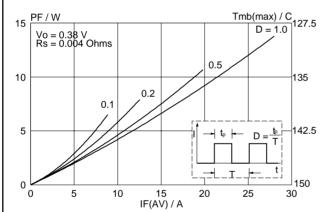


Fig.1. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; square current waveform where $I_{F(AV)} = I_{F(RMS)} x \sqrt{D}$.

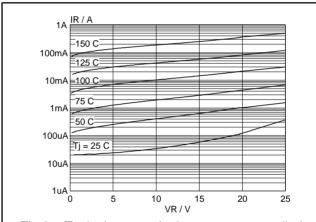


Fig.3. Typical reverse leakage current per diode; $I_R = f(V_R)$; parameter T_j

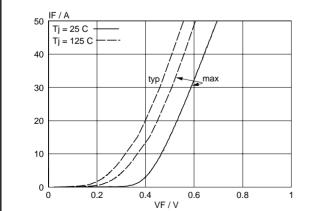


Fig.2. Typical and maximum forward characteristic $I_F = f(V_F)$; parameter T_i

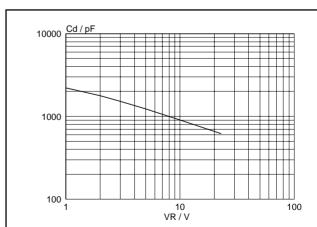
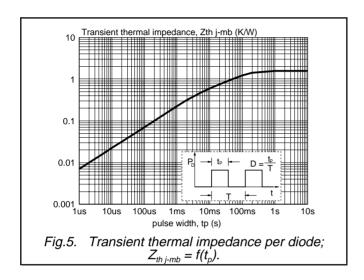


Fig.4. Typical junction capacitance per diode; $C_d = f(V_R)$; f = 1 MHz; $T_j = 25$ °C to 125 °C.

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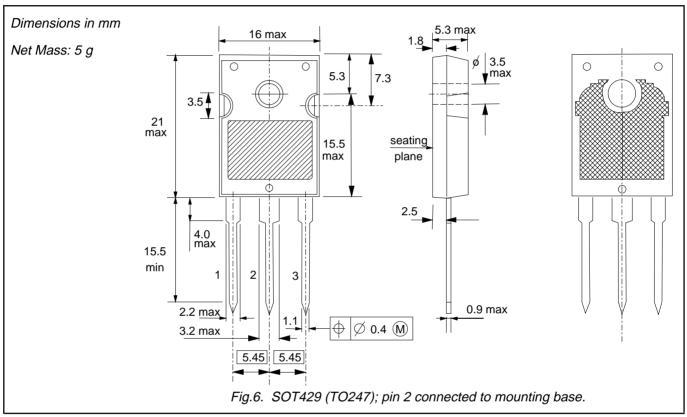
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MECHANICAL DATA



- Refer to mounting instructions for SOT429 envelope.
 Epoxy meets UL94 V0 at 1/8".

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Rectifier	diodes
schottky	barrier

PBYR4025WT series

DEFINITIONS

Data sheet status				
Objective specification	This data sheet contains target or goal specifications for product development.			
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.			
Product specification	This data sheet contains final product specifications.			
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Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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